	Hits	Search Text	DBs
1	2	((resist or photoresist or photolithograph$5 or lithograph$5) same (mask or pattern) same lift$4off) and (MR or GMR or (spin near6 valve) or (magnetic near9 head) or read$6head) and ((resist or photoresist) same (pattern or mask) same (ion near9 (beam or gun or source)) same (etch$4 or irradiat$4 or harden$6 or cur$4)) and ((resist or photoresist) same ozone same lift$4off)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
2	6	((resist or photoresist or photolithograph$5 or lithograph$5) same (mask or pattern) same lift$4off) and (MR or GMR or (spin near6 valve) or (magnetic near9 head) or read$6head) and ((resist or photoresist) same (pattern or mask) same (ion near9 (beam or gun or source)) same (etch$4 or irradiat$4 or harden$6 or cur$4)) and ((resist or photoresist) same ozone)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
3	0	((resist or photoresist or photolithograph$5 or lithograph$5) same (mask or pattern) same lift$4off) and (MR or GMR or (spin near6 valve) or (magnetic near9 head) or read$6head) and ((resist or photoresist) same (pattern or mask) same (ion near9 (beam or gun or source)) same (etch$4 or irradiat$4 or harden$6 or cur$4)) and ((resist or photoresist) same (oxidation or ozone or oxidi$4) same treat$5 same lift$5off)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
4	5	((resist or photoresist or photolithograph$5 or lithograph$5) same (mask or pattern) same lift$4off) and (MR or GMR or (spin near6 valve) or (magnetic near9 head) or read$6head) and ((resist or photoresist) same (pattern or mask) same (ion near9 (beam or gun or source)) same (etch$4 or irradiat$4 or harden$6 or cur$4)) and ((resist or photoresist) same (oxidation or ozone or oxidi$4) same treat$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
5	15	((resist or photoresist or photolithograph$5 or lithograph$5) same (mask or pattern) same lift$4off) and (MR or GMR or (spin near6 valve) or (magnetic near9 head) or read$6head) and ((resist or photoresist) same (pattern or mask) same (ion near9 (beam or gun or source)) same (etch$4 or irradiat$4 or harden$6 or cur$4)) and ((resist or photoresist) same (oxidation or ozone or oxidi$4)) and ((resist or photoresist) same (mask or pattern$4) same (sputter$4 or deposit$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
6	2	((resist or photoresist or photolithograph$5 or lithograph$5) same (mask or pattern) same lift$4off) and (MR or GMR or (spin near6 valve) or (magnetic near9 head) or read$6head) and ((resist or photoresist) same (pattern or mask) same (ion near9 (beam or gun or source)) same (etch$4 or irradiat$4 or harden$6 or cur$4)) and ((resist or photoresist) same (oxidation or ozone or oxidi$4)) and ((resist or photoresist) same (mask or pattern$4) same (sputter$4 or deposit$4 or coat$4 or layer or form$4)) and ((ion near9 (beam or gun or source)) same (voltage or volt)) and ((resist or photoresist) same (thickness or thick$4 or nm))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
7	2	((resist or photoresist or photolithograph$5 or lithograph$5) same (mask or pattern) same lift$4off) and (MR or GMR or (spin near6 valve) or (magnetic near9 head) or read$6head) and ((resist or photoresist) same (pattern or mask) same (ion near9 (beam or gun or source)) same (etch$4 or irradiat$4 or harden$6 or cur$4)) and ((resist or photoresist) same (oxidation or ozone or oxidi$4 or passivat$5)) and ((ion near9 (beam or gun or source)) same (voltage or volt)) and ((resist or photoresist) same (thickness or thick$4 or nm))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
8	24	((resist or photoresist or photolithograph$5 or lithograph$5) same (mask or pattern) same lift$4off) and ((resist or photoresist) same (pattern or mask) same (ion near9 (beam or gun or source)) same (etch$4 or irradiat$4 or harden$6 or cur$4)) and ((resist or photoresist) same (oxidation or ozone or oxidi$4 or passivat$5)) and ((ion near9 (beam or gun or source)) same (voltage or volt)) and ((resist or photoresist) same (thickness or thick$4 or nm))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
9	22	S8 NOT S5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
10	46	((resist or photoresist) same (pattern or mask) same (ion near9 (beam or gun or source)) same (etch$4 or irradiat$4 or harden$6 or cur$4)) and ((resist or photoresist) same (oxidation or ozone or oxidi$4 or passivat$5) same (plasma or ion$4beam)) and ((ion near9 (beam or gun or source)) same (voltage or volt)) and ((resist or photoresist) same (thickness or thick$4 or nm))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
11	15	((resist or photoresist or photolithograph$5 or lithograph$5) same (mask or pattern) same lift$4off) and (MR or GMR or (spin near6 valve) or (magnetic near9 head) or read$6head) and ((resist or photoresist) same (pattern or mask) same (ion near9 (beam or gun or source)) same (etch$4 or irradiat$4 or harden$6 or cur$4)) and ((resist or photoresist) same (oxidation or ozone or oxidi$4)) and ((resist or photoresist) same (mask or pattern$4) same (sputter$4 or deposit$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
12	24	((resist or photoresist or photolithograph$5 or lithograph$5) same (mask or pattern) same lift$4off) and ((resist or photoresist) same (pattern or mask) same (ion near9 (beam or gun or source)) same (etch$4 or irradiat$4 or harden$6 or cur$4)) and ((resist or photoresist) same (oxidation or ozone or oxidi$4 or passivat$5)) and ((ion near9 (beam or gun or source)) same (voltage or volt)) and ((resist or photoresist) same (thickness or thick$4 or nm))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
13	22	S12 NOT S11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
14	37	S10 NOT S13	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
15	5	((resist or photoresist) same (pattern or mask) same (ion near9 (beam or gun or source)) same (expos$4 or irradiat$4 or harden$6 or cur$4)) and ((resist or photoresist or pattern) same ozone same (plasma or ion$4beam or treat$4 or passivat$)) and ((resist or photoresist) same (mask or pattern) same ((bottom near9 width) or (bottom near9 portion) or undercut$4 or shadow$4 or overhang$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
16	12	((resist or photoresist or photolithograph$5 or lithograph$5) near14 (mask or pattern) near28 lift$4off near22 (thickness or thick) near29 (overhang or undercut or shadow))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
17	6	((resist or photoresist or photolithograph$5 or lithograph$5) same (mask or pattern) same lift$4off same (overhang or undercut or shadow) same (ion$5beam or (ion2 near9 expos$4)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
18	1	(((resist or photoresist) near14 (mask or pattern) near26 ((ion near5 beam) or (ion near6 expos$4)) near26 volt$4) same lift$5off)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
19	18	((resist or photoresist or photolithograph$5 or lithograph$5) same (mask or pattern) same lift$4off same ozone)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
20	31	((resist or photoresist or photolithograph$5 or lithograph$5) same (mask or pattern) same ozone) and (lift$5off same (resist or photoresist or mask or pattern))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
21	13	S23 NOT S22	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
22	15	((resist or photoresist or photolithograph$5 or lithograph$5) same (mask or pattern) same ozone same treat$4) and lift$5off and ((plasma or irradiat$4 or expos$$ or illuminat$4) same (oxygen or ozone))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
23	4	((resist or photoresist or photolithograph$5 or lithograph$5) same (mask or pattern) same ozone same treat$4) and lift$5off and ((plasma or irradiat$4 or expos$$ or illuminat$4) same (oxygen or ozone)) and (((flow near12 rate) or rate) same ozone)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
24	26	((resist or photoresist) same ozone same treat$4) and lift$5off and ((plasma or irradiat$4 or expos$4 or illuminat$4) same (oxygen or ozone))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
25	2	((resist or photoresist) same oxid$5 same treat$4) and lift$5off and ((plasma or irradiat$4 or expos$4 or illuminat$4) same (oxygen or ozone)) and (develop$4 same (NMP or (methyl near5 pyrrolidone)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB